High-Power NPN Silicon Transistor

This transistor is for use as an output device in complementary audio amplifiers to 100–Watts music power per channel.

Features

- High DC Current Gain $h_{FE} = 25-100$ @ $I_C = 7.5$ A
- Excellent Safe Operating Area
- Complement to the PNP MJ4502
- Pb-Free Package is Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CER}	100	Vdc
Collector-Base Voltage	V _{CB}	100	Vdc
Collector–Emitter Voltage	V _{CEO}	90	Vdc
Emitter-Base Voltage	V _{EB}	4.0	Vdc
Collector Current	I _C	30	Adc
Base Current	I _B	7.5	Adc
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	200 1.14	W W/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +200	°C

THERMAL CHARACTERISTICS

Characteristics	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$\theta_{\sf JC}$	0.875	°C/W

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.



ON Semiconductor®

http://onsemi.com

30 AMPERE POWER TRANSISTOR NPN SILICON 100 VOLTS – 200 WATTS



TO-204AA (TO-3) CASE 1-07 STYLE 1

MARKING DIAGRAM



MJ802 = Device Code G = Pb-Free Package A = Assembly Location

YY = Year WW = Work Week MEX = Country of Origin

ORDERING INFORMATION

Device	Package	Shipping
MJ802	TO-204	100 Units / Tray
MJ802G	TO-204 (Pb-Free)	100 Units / Tray

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	1		ı	1
Collector–Emitter Breakdown Voltage (I_C = 200 mAdc, R_{BE} = 100 Ω)	BV _{CER}	100	_	Vdc
Collector–Emitter Sustaining Voltage (Note 1) (I _C = 200 mAdc)	V _{CEO(sus)}	90	_	Vdc
Collector–Base Cutoff Current $(V_{CB} = 100 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 100 \text{ Vdc}, I_E = 0, T_C = 150 ^{\circ}\text{C})$	Ісво	- -	1.0 5.0	mAdc
Emitter–Base Cutoff Current $(V_{BE} = 4.0 \text{ Vdc}, I_C = 0)$	I _{EBO}	-	1.0	mAdc
ON CHARACTERISTICS ⁽¹⁾				•
DC Current Gain (Note 1) ($I_C = 7.5 \text{ Adc}$, $V_{CE} = 2.0 \text{ Vdc}$)	h _{FE}	25	100	-
Base–Emitter "On" Voltage ($I_C = 7.5 \text{ Adc}$, $V_{CE} = 2.0 \text{ Vdc}$)	V _{BE(on)}	-	1.3	Vdc
Collector–Emitter Saturation Voltage (I _C = 7.5 Adc, I _B = 0.75 Adc)	V _{CE(sat)}	-	0.8	Vdc
Base–Emitter Saturation Voltage (I _C = 7.5 Adc, I _B = 0.75 Adc)	V _{BE(sat)}	_	1.3	Vdc
DYNAMIC CHARACTERISTICS	·		•	
Current Gain – Bandwidth Product (I _C = 1.0 Adc, V _{CE} = 10 Vdc, f = 1.0 MHz)	f _T	2.0	_	MHz

^{1.} Pulse Test: Pulse Width $\leq 300 \,\mu\text{s}$, Duty Cycle $\leq 2.0\%$.

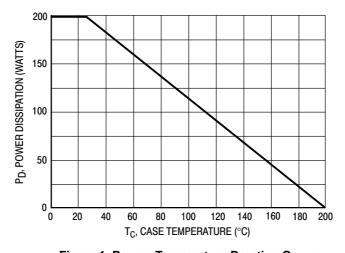


Figure 1. Power-Temperature Derating Curve

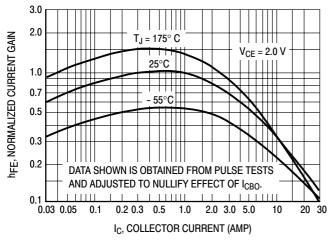


Figure 2. DC Current Gain

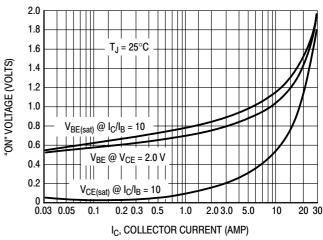


Figure 3. "On" Voltages

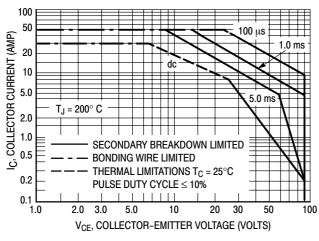
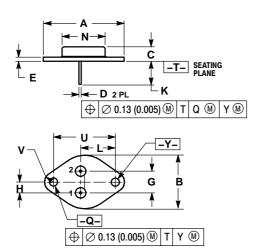


Figure 4. Active Region Safe Operating Area

The Safe Operating Area Curves indicate $I_C - V_{CE}$ limits below which the device will not enter secondary breakdown. Collector load lines for specific circuits must fall within the applicable Safe Area to avoid causing a catastrophic failure. To insure operation below the maximum T_J , power temperature derating must be observed for both steady state and pulse power conditions.

PACKAGE DIMENSIONS

TO-204 (TO-3) **CASE 1-07** ISSUE Z



- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.
 3. ALL RULES AND NOTES ASSOCIATED WITH REFERENCED TO-204AA OUTLINE SHALL APPLY.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	1.550 REF		39.37	REF	
В		1.050		26.67	
C	0.250	0.335	6.35	8.51	
D	0.038	0.043	0.97	1.09	
E	0.055	0.070	1.40	1.77	
G	0.430 BSC		10.92 BSC		
Н	0.215 BSC		5.46 BSC		
K	0.440	0.480	11.18	12.19	
L	0.665 BSC		16.89 BSC		
N		0.830		21.08	
Q	0.151	0.165	3.84	4.19	
U	1.187 BSC		30.15 BSC		
٧	0.131	0.188	3.33	4.77	

STYLE 1: PIN 1. BASE 2. EMITTER CASE: COLLECTOR

ON Semiconductor and una are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice on semiconductor and are registered readerlands of semiconductor Components industries, Ltc (SCILLC). Solitude services the inject to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 61312, Phoenix, Arizona 85082-1312 USA Phone: 480-829-7710 or 800-344-3860 Toll Free USA/Canada Fax: 480-829-7709 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free

Japan: ON Semiconductor, Japan Customer Focus Center 2-9-1 Kamimeguro, Meguro-ku, Tokyo, Japan 153-0051 Phone: 81-3-5773-3850

ON Semiconductor Website: http://onsemi.com

Order Literature: http://www.onsemi.com/litorder

For additional information, please contact your local Sales Representative.